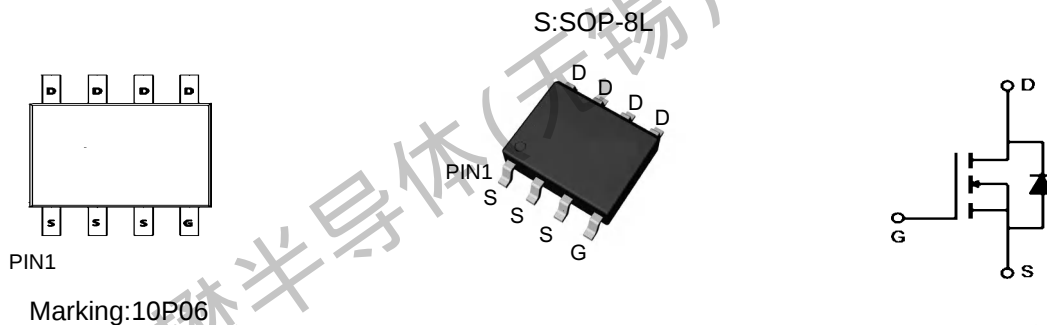


TM10P06S

P-Channel Enhancement Mosfet

General Description • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant Applications • Load switch • PWM	General Features $V_{DS} = -60V$ $I_D = -10A$ $R_{DS(ON)} = 24 m\Omega$ (typ.) @ $V_{GS} = -10V$ 100% UIS Tested 100% R_g Tested 
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Absolute Maximum Ratings ($T_A = 25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-10	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-7.0	A
I_{DM}	Pulsed Drain Current ²	-38	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ⁴	4.1	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	80	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	25	$^\circ C/W$

TM10P06S
P-Channel Enhancement Mosfet
Electrical Characteristics: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μA	-60	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =-60V	---	---	-1	μA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0A	---	---	±100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μA	-1	-2	-3	V
R _{DS(on)}	Drain-Source On Resistance②	V _{GS} =-10V, I _D =-15A	---	24	29	mΩ
		V _{GS} =-4.5V, I _D =-10A	---	30	39	
G _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-15A	---	35	---	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-25V, V _{GS} =0V, f=1MHz	---	2025	---	pF
C _{oss}	Output Capacitance		---	133	---	
C _{rss}	Reverse Transfer Capacitance		---	97	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} =-30V R _{GEN} =3Ω, V _{GS} =-10V	---	12	---	ns
t _r	Rise Time		---	9	---	ns
t _{d(off)}	Turn-Off Delay Time		---	63	---	ns
t _f	Fall Time		---	13	---	ns
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-30V, I _D =-20A	---	53	---	nC
Q _{gs}	Gate-Source Charge		---	10	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	12	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Source-Drain Diode Forward Voltage ³	V _{GS} =0V, I _S =-15A, T _J =25℃	---	-0.88	-1.2	V
I _S	Continuous Drain Current	V _D =V _G =0V	---	-10	---	V
I _{SM}	Pulsed Drain Current	V _D =V _G =0V	---	-5.2	---	V
t _{rr}	Reverse Recovery Time	I _S =-20A, V _{GS} =0V	---	26	---	ns
Q _{rr}	Reverse Recovery Charge	.dI/dt=-500A/μs	---	29	---	nC

Notes:

1.Repetitive Rating: Pulse width limited by maximum junction temperature.

 2. E_{AS} condition: $T_J=25^\circ\text{C}, V_{DD}=40V, V_G=-10V, R_g=25\Omega, L=0.5mH$.

3.Repetitive Rating: Pulse width limited by maximum junction temperature.

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Typical Characteristics

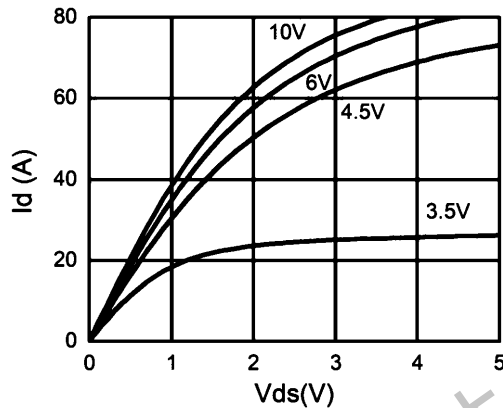


Figure 1. Output Characteristics

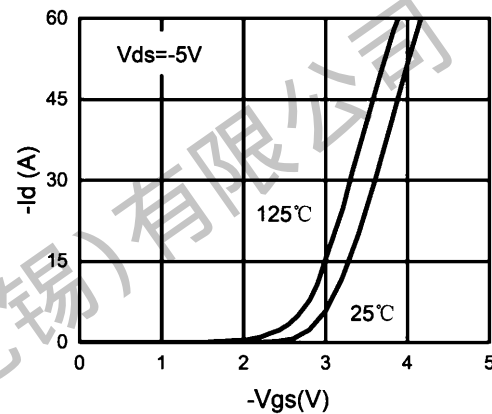


Figure 2. Transfer Characteristics

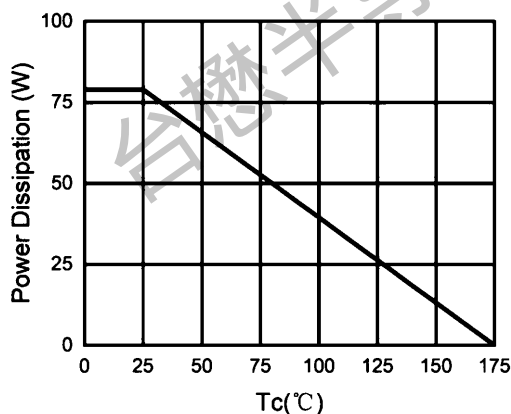


Figure 3. Power Dissipation

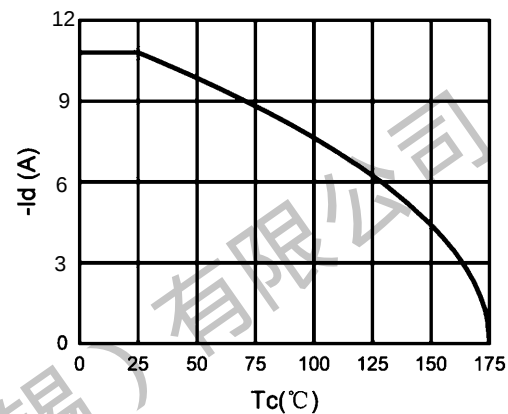


Figure 4. Drain Current

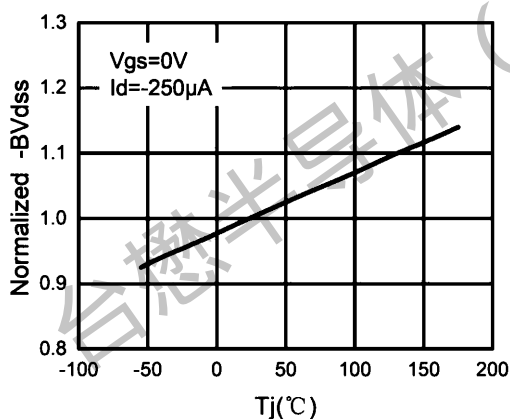


Figure 5. BV_{DSS} vs Junction Temperature

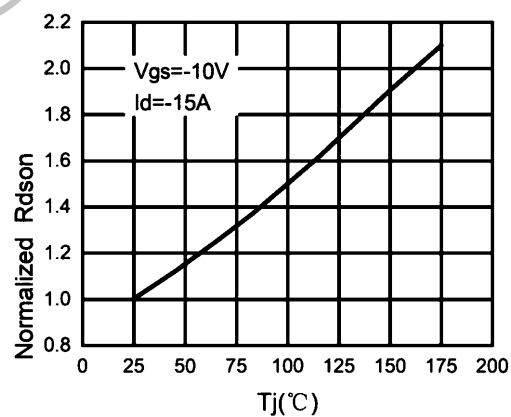


Figure 6. $R_{DS(ON)}$ vs Junction Temperature

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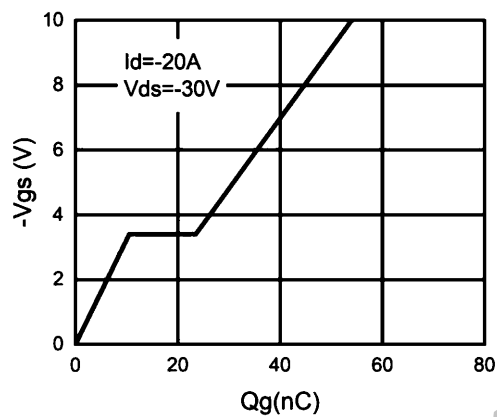


Figure 7. Gate Charge Waveforms

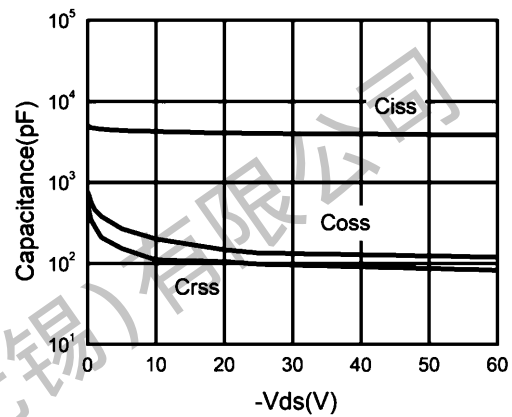


Figure 8. Capacitance

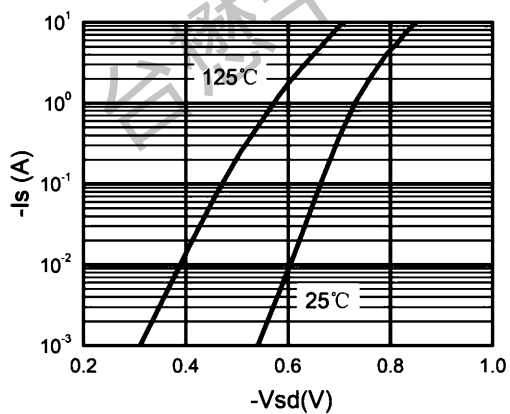


Figure 9. Body-Diode Characteristics

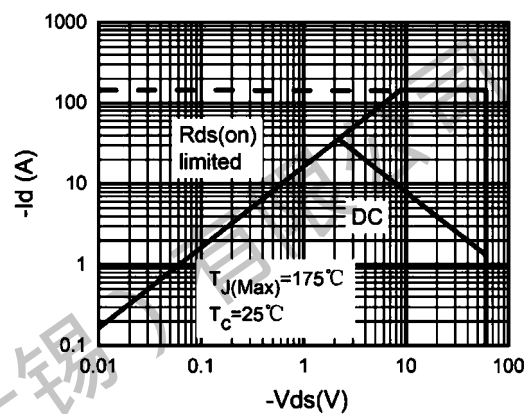
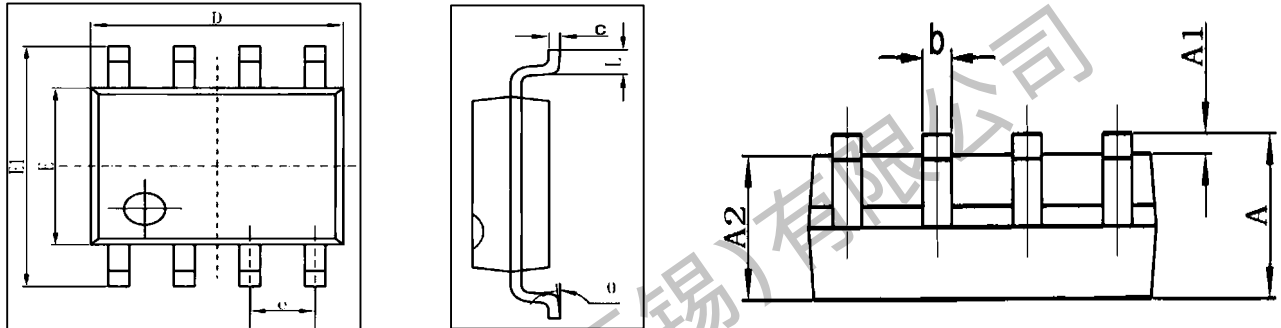


Figure 10. Maximum Safe Operating Area

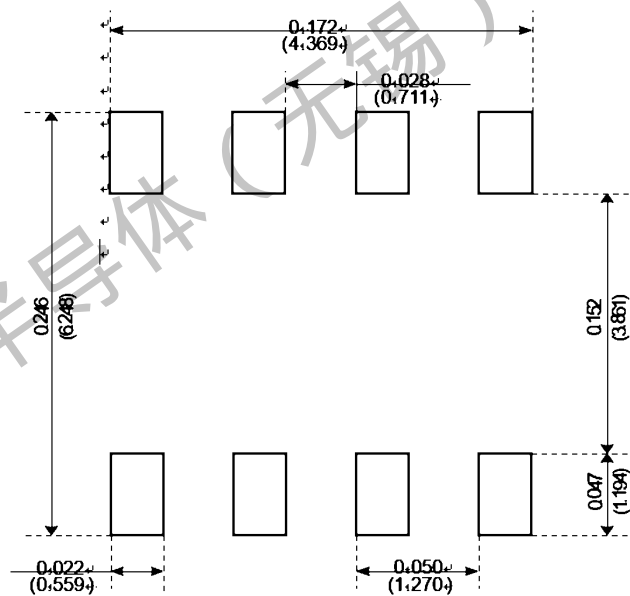
TM10P06S

P-Channel Enhancement Mosfet

Package Mechanical Data:SOP-8L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

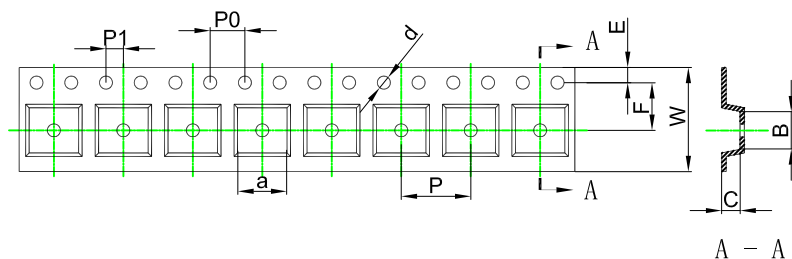


Recommended Minimum Pads

TM10P06S

P-Channel Enhancement Mosfet

SOP-8L Embossed Carrier Tape



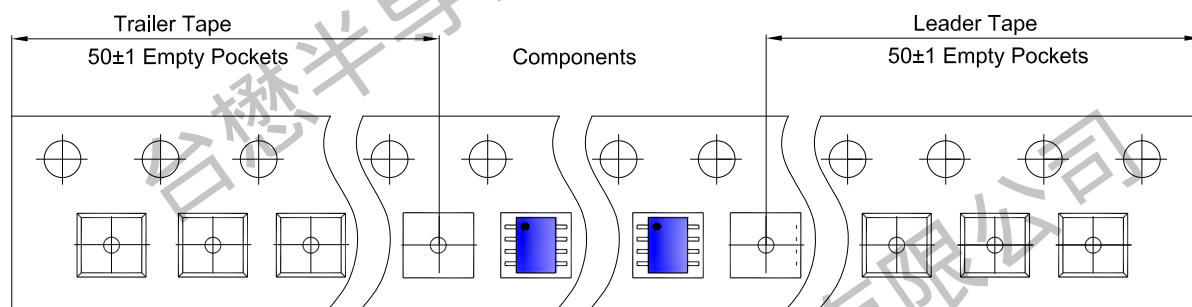
Packaging Description:

SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

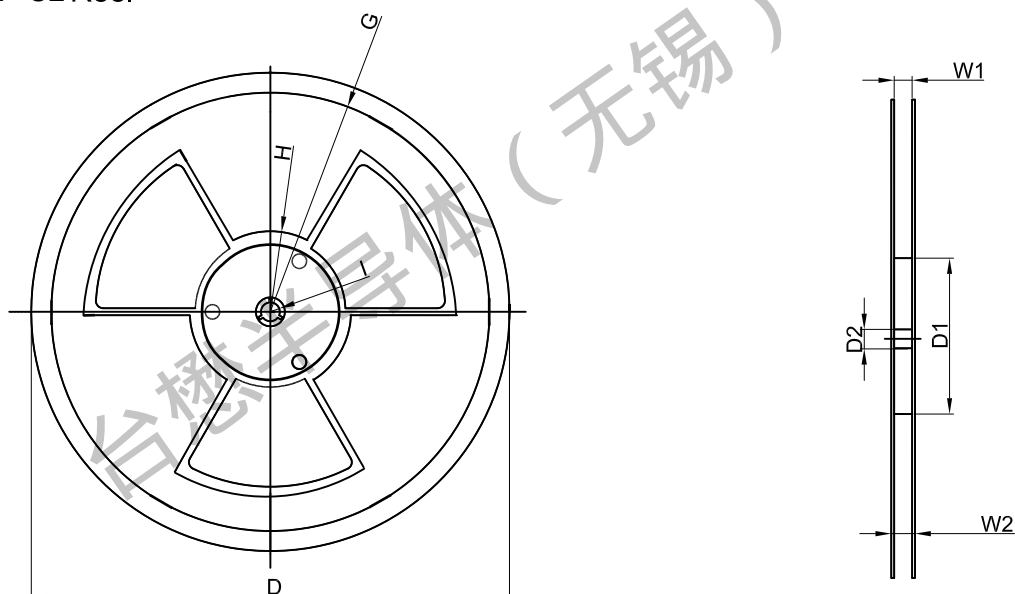
ALL DIM IN mm

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
SOP-8L	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

SOP-8L Tape Leader and Trailer



SOP-8L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13"Dia	Ø330.00	100.00	13.00	R135.00	R55.00	R6.50	12.00	14.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3,000 pcs	13 inch	6,000 pcs	370×355×52	48,000 pcs	400×360×368	

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Revision history:

Date	Rev	Description	Page
2023.12.11	23.12	Original	